PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

Rev. 02 — 2 September 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP resistor-equipped transistors

Table 1.	Product	overview
		0.0.0.0.0

Type number	Package		Package		NPN/PNP	NPN/NPN
	NXP	JEITA	complement	complement		
PEMB24	SOT666	-	PEMD24	PEMH24		
PUMB24	SOT363	SC-88	PUMD24	PUMH24		

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current (DC)		-	-	-20	mA
R1	bias resistor 1 (input)		70	100	130	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



1

| | 2 3 *006aaa212*

PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

Table 4. Ordering information				
Type number	Package			
	Name	Description	Version	
PEMB24	-	plastic surface mounted package; 6 leads	SOT666	
PUMB24	SC-88	plastic surface mounted package; 6 leads	SOT363	
PUMB24	SC-88	plastic surface mounted package; 6 leads	S	

4. Marking

Marking code ^[1]
6M
T7*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong * = t: made in Malaysia

* = W: made in China

PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-40	V
lo	output current (DC)		-	-20	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		<u>[1] [2]</u> _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device	;				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

[1] Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \leq 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1] [2] _	-	625	K/W
Per device	9					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> _	-	416	K/W
	SOT666		[1] [2] _	-	416	K/W

[1] Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	-1	μA
	cut-off current	V _{CE} = -30 V; I _B = 0 A; T _j = 150 °C	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-50	μΑ
h _{FE}	DC current gain	V_{CE} = -5 V; I _C = -5 mA	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -5 \text{ mA}; I_{B} = -0.25 \text{ mA}$	-	-	-150	mV
V _{I(off)}	off-state input voltage	V_{CE} = -5 V; I_C = -100 μ A	-	-1.2	-0.5	V
V _{I(on)}	on-state input voltage	V_{CE} = -0.3 V; I _C = -1 mA	-3	-1.6	-	V
R1	bias resistor 1 (input)		70	100	130	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz	-	-	2.5	pF

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PEMB24; PUMB24

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PEMB24 PUMB24 2

PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

8. Package outline



Fig 5. Package outline SOT363 (SC-88)

PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω



Fig 6. Package outline SOT666

PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description		Packing qua	ntity	
				3000	4000	10000
PEMB24	SOT666	4 mm pitch, 8 mm tape and reel		-	-115	-
PUMB24	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-135
PUMB24	SOT363	4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

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10. Revision history

Table 10. Revision histo	ory					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMB24_PUMB24_2	20090902	Product data sheet	-	PEMB24_PUMB24_1		
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 					
	 Figure 5 "Package outline SOT363 (SC-88)": updated 					
	Figure 6 "Packa	age outline SOT666": upo	lated			
PEMB24_PUMB24_1	20050218	Product data sheet	-	-		

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11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMB24_PUMB24_2
Product data sheet

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PEMB24; PUMB24

PNP/PNP resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

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